UVA Sensor: LD-G360-100S



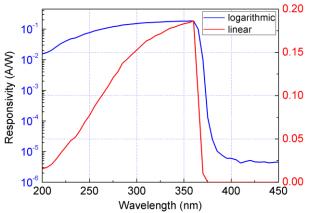
| Features | Indium Gallium nitride based material | | | |
|--------------|--|--|--|--|
| | Broad band UVA+UVB+UVC photodiode | | | |
| | Photovoltaic mode operation | | | |
| | SMD3535 package | | | |
| | Good visible blindness High responsivity and low dark current | | | |
| | | | | |
| | | | | |
| Applications | UV LED monitoring | | | |
| | UV radiation dose measurement | | | |

UV Curing

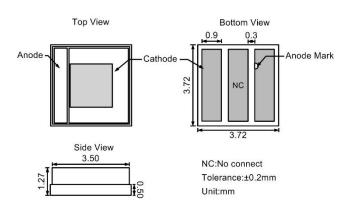
Specifications

| Parameter | Symbol | Value | Unit | |
|---|-------------------|------------------|-----------------|--|
| Spectral characteristics (25 °C) | | | | |
| Wavelength of peak responsivisity | λ_{max} | 360 | nm | |
| Peak responsivisity (at 360 nm) | R _{max} | 0.18 | A/W | |
| Spectral response range | - | 180~370 | nm | |
| UV/visible rejection ratio (R _{max} /R _{400 nm}) | VB | >10 ⁴ | - | |
| General characteristics (25 °C) | | | | |
| Chip size | А | 1 | mm ² | |
| Dark current (1 V reverse bias) | ۱ _d | <1 | nA | |
| Capacitance (at 0 V and 1 MHz) | С | 23 | pF | |
| Temperature coefficient | T _c | -0.1 | %/°C | |
| Maximum ratings | | | | |
| Operation temperature range | T _{opt} | -40~85 | °C | |
| Storage temperature range | T _{stor} | -40~85 | °C | |
| Soldering temperature (3 s) | T _{sold} | 260 | ٥C | |
| Reverse voltage | V _{Rmax} | 10 | V | |

Spectral response



Package dimensions



*Caution: ESD can damage the device hence please avoid ESD.